

-30V, -11A, 12mΩ Dual P-channel Power Trench MOSFET

JMTP160P03D

Features

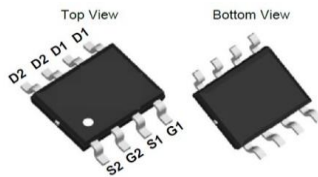
- Excellent $R_{DS(ON)}$ and Low Gate Charge
- 100% UIS Tested
- Halogen-free; RoHS-compliant
- Pb-free plating

Applications

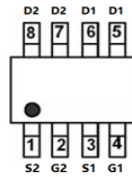
- Load Switch
- PWM Application
- Power Management

Product Summary

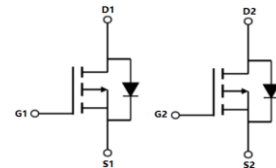
Parameters	Value	Unit
V_{DSS}	-30	V
$V_{GS(th_Typ)}$	-1.7	V
$I_D(@V_{GS}=10V)$	-11	A
$R_{DS(ON_Typ)}(@V_{GS}=-10V)$	12	mΩ
$R_{DS(ON_Typ)}(@V_{GS}=-4.5V)$	16	mΩ



SOP-8L_Dual



Pin Assignment



Schematic Diagram

Ordering Information

Device	Marking	MSL	Form	Package	Reel(pcs)	Per Carton (pcs)
JMTP160P03D	160P03D	3	Tape&Reel	SOP-8	4000	48000

Absolute Maximum Ratings (@ $T_A = 25^\circ\text{C}$ unless otherwise specified)

Symbol	Parameter	Value	Unit
V_{DS}	Drain-to-Source Voltage	-30	V
V_{GS}	Gate-to-Source Voltage	± 20	V
I_D	Continuous Drain Current	$T_A = 25^\circ\text{C}$	-11
		$T_A = 100^\circ\text{C}$	-7
I_{DM}	Pulsed Drain Current ⁽¹⁾	Refer to Fig.4	A
E_{AS}	Single Pulsed Avalanche Energy ⁽²⁾	65	mJ
P_D	Power Dissipation	$T_A = 25^\circ\text{C}$	2.8
		$T_A = 100^\circ\text{C}$	1.1
T_J, T_{STG}	Junction & Storage Temperature Range	-55 to 150	$^\circ\text{C}$

Thermal Characteristics

Symbol	Parameter	Max	Unit
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient ⁽³⁾	112	$^\circ\text{C}/\text{W}$
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient ⁽⁴⁾	45	

**Electrical Characteristics** ($T_J = 25^\circ\text{C}$ unless otherwise specified)

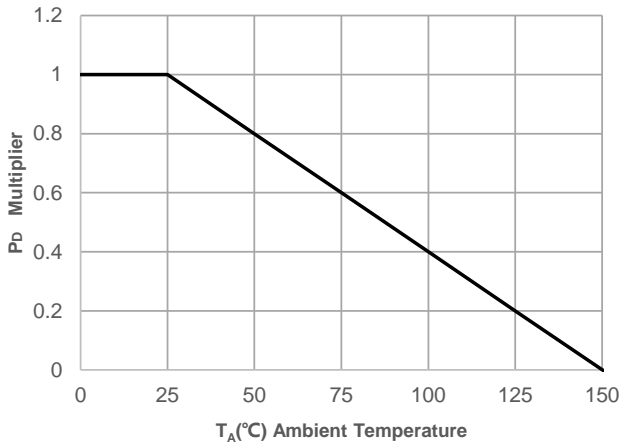
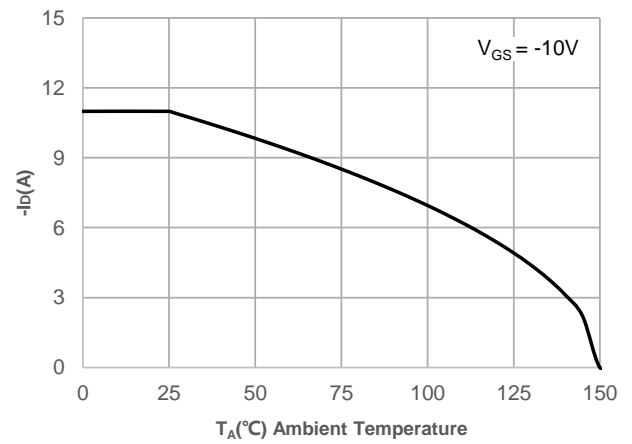
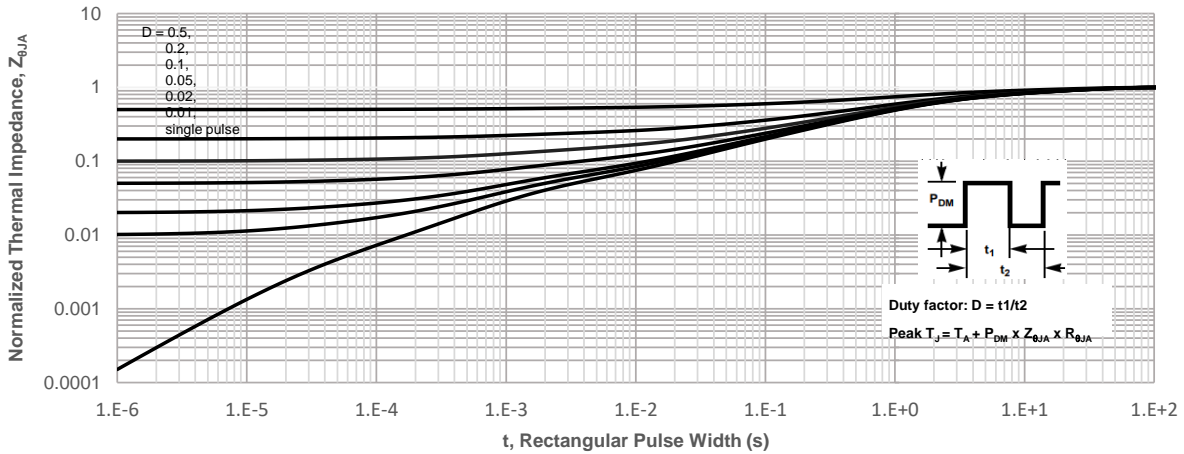
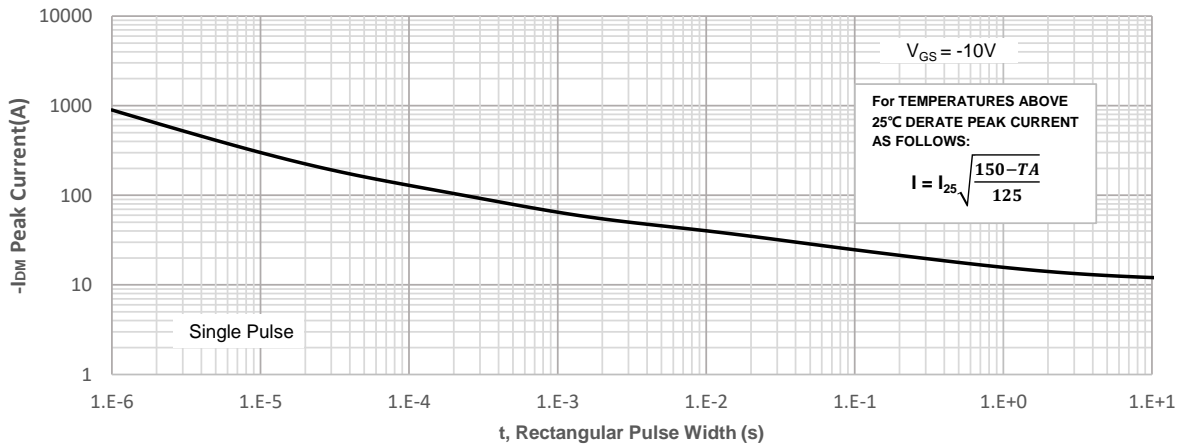
Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
Off Characteristics						
$V_{(BR)DSS}$	Drain-Source Breakdown Voltage	$I_D = -250\mu\text{A}$, $V_{GS} = 0\text{V}$	-30	-	-	V
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = -30\text{V}$, $V_{GS} = 0\text{V}$	-	-	-1.0	μA
I_{GSS}	Gate-Body Leakage Current	$V_{DS} = 0\text{V}$, $V_{GS} = \pm 20\text{V}$	-	-	± 100	nA
On Characteristics						
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}$, $I_D = -250\mu\text{A}$	-1.2	-1.7	-2.2	V
$R_{DS(ON)}$	Static Drain-Source ON-Resistance ⁽⁵⁾	$V_{GS} = -10\text{V}$, $I_D = -10\text{A}$	-	12	17	m Ω
		$V_{GS} = -4.5\text{V}$, $I_D = -5\text{A}$	-	16	27	m Ω
Dynamic Characteristics						
R_g	Gate Resistance	$f = 1\text{MHz}$	-	7	-	Ω
C_{iss}	Input Capacitance	$V_{GS} = 0\text{V}$, $V_{DS} = -15\text{V}$, $f = 1\text{MHz}$	1763	2468	3331	pF
C_{oss}	Output Capacitance		184	258	348	pF
C_{riss}	Reverse Transfer Capacitance		164	230	310	pF
Q_g	Total Gate Charge	$V_{GS} = 0$ to -10V $V_{DS} = -15\text{V}$, $I_D = -10\text{A}$	33	46	62	nC
Q_{gs}	Gate Source Charge		-	8.2	-	nC
Q_{gd}	Gate Drain("Miller") Charge		-	8.1	-	nC
Switching Characteristics						
$t_{d(on)}$	Turn-On DelayTime	$V_{GS} = -10\text{V}$, $V_{DD} = -30\text{V}$ $I_D = -9\text{A}$, $R_{GEN} = 3\Omega$	-	7	-	ns
t_r	Turn-On Rise Time		-	2	-	ns
$t_{d(off)}$	Turn-Off DelayTime		-	76	-	ns
t_f	Turn-Off Fall Time		-	33	-	ns
Body Diode Characteristics						
I_S	Maximum Continuous Body Diode Forward Current		-	-	-11	A
I_{SM}	Maximum Pulsed Body Diode Forward Current		-	-	-44	A
V_{SD}	Body Diode Forward Voltage	$V_{GS} = 0\text{V}$, $I_S = -10\text{A}$	-		-1.2	V
t_{rr}	Body Diode Reverse Recovery Time	$I_F = -10\text{A}$, $di/dt = 100\text{A}/\mu\text{s}$	10	14	19	ns
Q_{rr}	Body Diode Reverse Recovery Charge		-	5.3	-	nC

Notes:

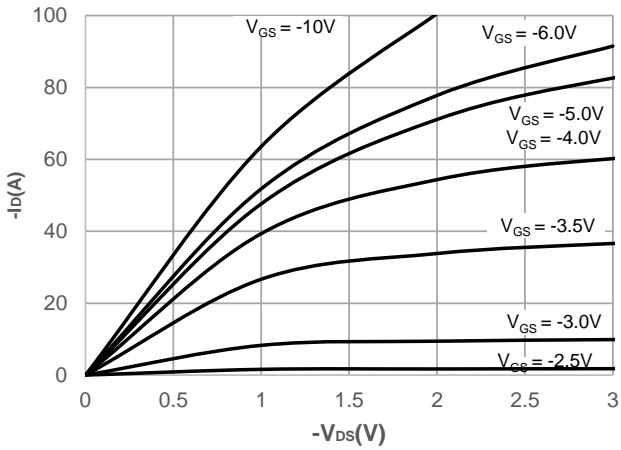
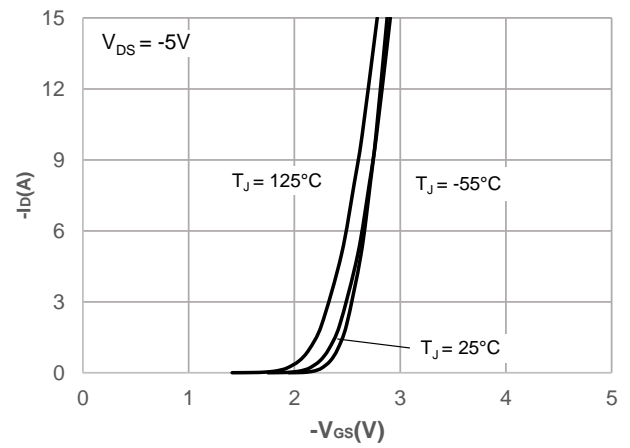
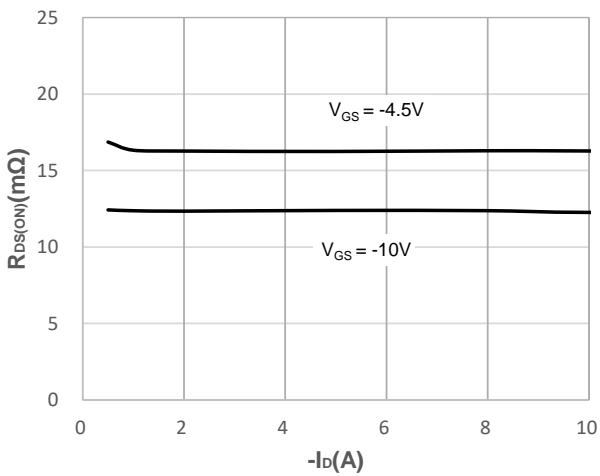
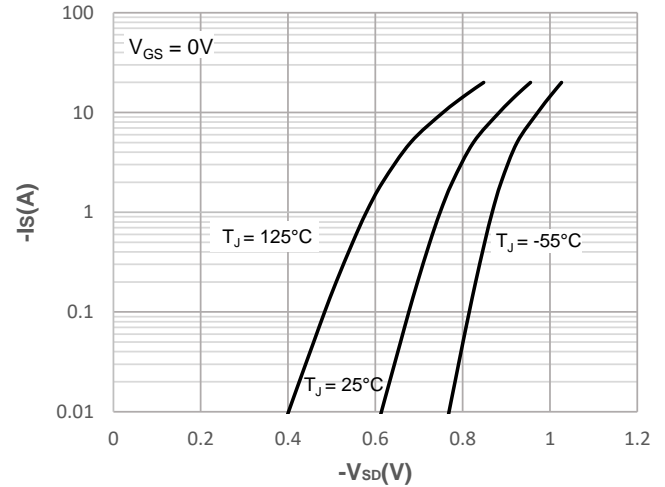
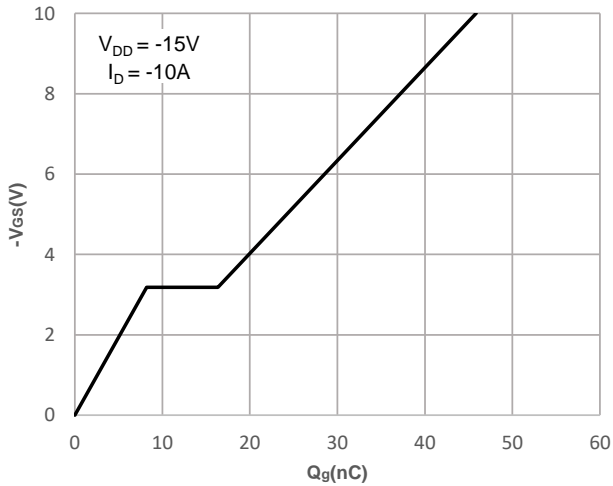
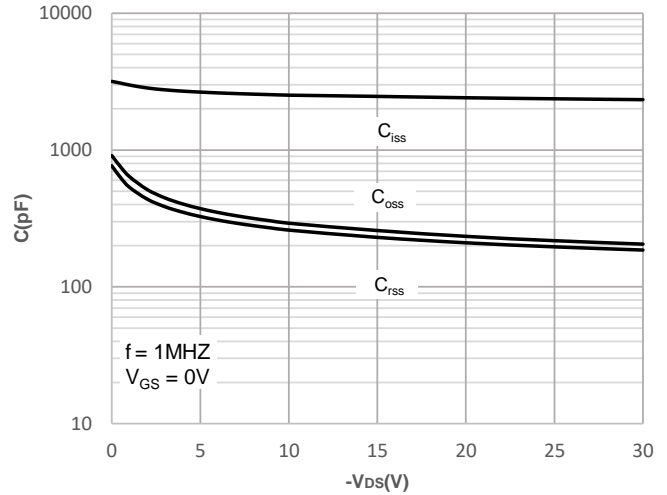
1. Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature.
2. E_{AS} condition: Starting $T_J = 25^\circ\text{C}$, $V_{DD} = -15\text{V}$, $V_{GS} = -10\text{V}$, $R_G = 25\text{ohm}$, $L = 0.5\text{mH}$, $I_{AS} = -16.1\text{A}$, $V_{DD} = 0\text{V}$ during time in avalanche.
3. $R_{\theta JA}$ is measured with the device mounted on a minimum recommended pad of 2oz copper FR4 PCB.
4. $R_{\theta JA}$ is measured with the device mounted on a 1inch² pad of 2oz copper FR4 PCB.
5. Pulse Test: Pulse Width $\leq 300\mu\text{s}$, Duty Cycle $\leq 0.5\%$.



Typical Performance Characteristics

Figure 1: Power De-rating

Figure 2: Current De-rating

Figure 3: Normalized Maximum Transient Thermal Impedance

Figure 4: Peak Current Capacity


Typical Performance Characteristics

Figure 5: Output Characteristics

Figure 6: Typical Transfer Characteristics

Figure 7: On-resistance vs. Drain Current

Figure 8: Body Diode Characteristics

Figure 9: Gate Charge Characteristics

Figure 10: Capacitance Characteristics


Typical Performance Characteristics

Figure 11: Normalized Breakdown voltage vs. Junction Temperature

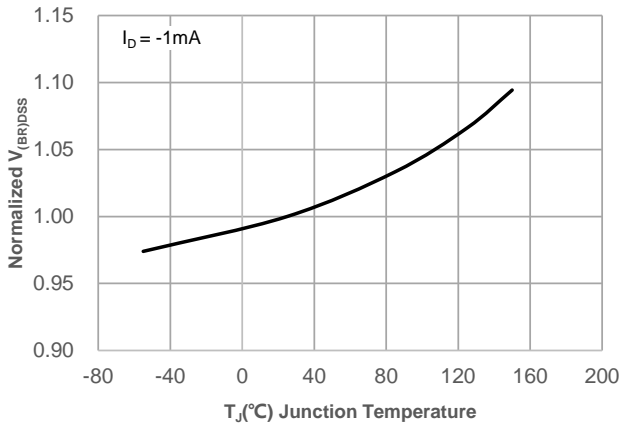


Figure 12: Normalized on Resistance vs. Junction Temperature

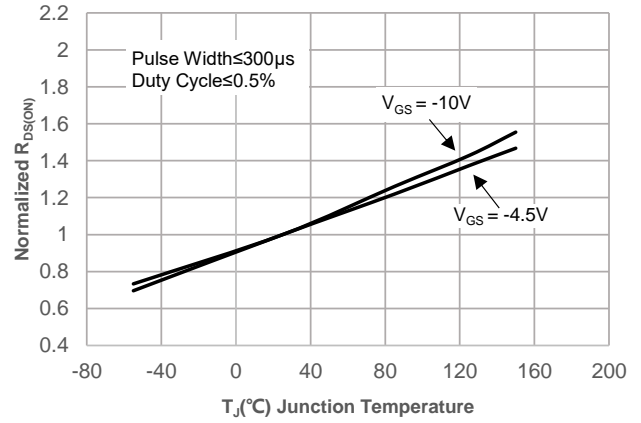


Figure 13: Normalized Threshold Voltage vs. Junction Temperature

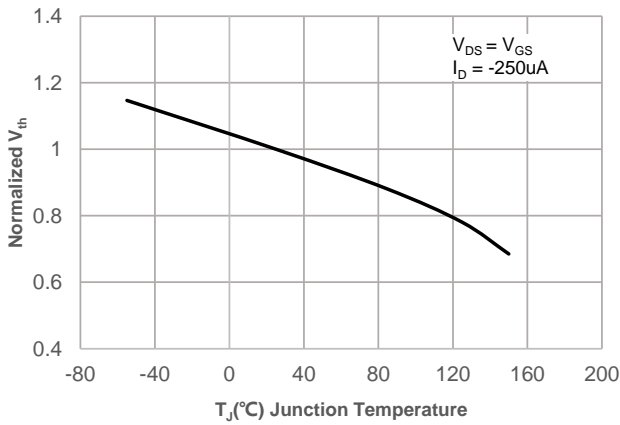


Figure 14: R_{DS(ON)} vs. V_{GS}

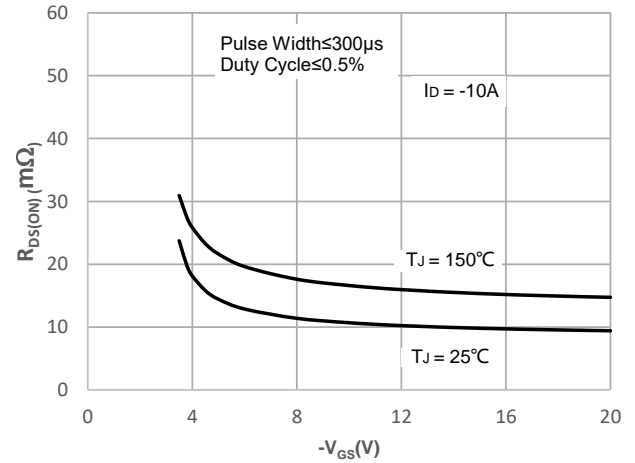
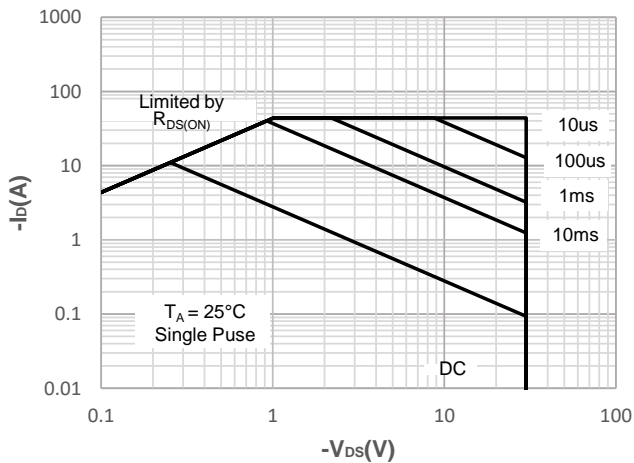


Figure 15: Maximum Safe Operating Area



Test Circuit

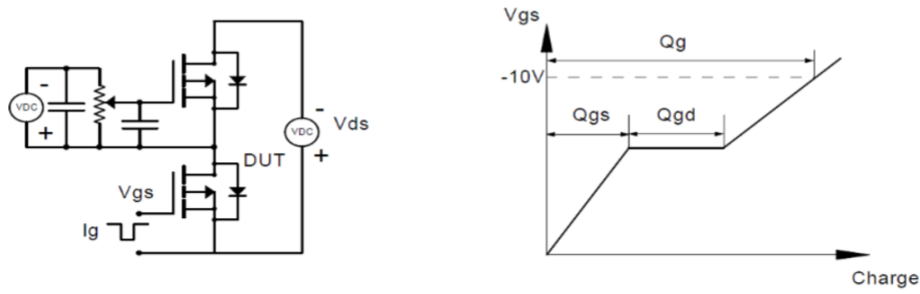


Figure 1: Gate Charge Test Circuit & Waveform

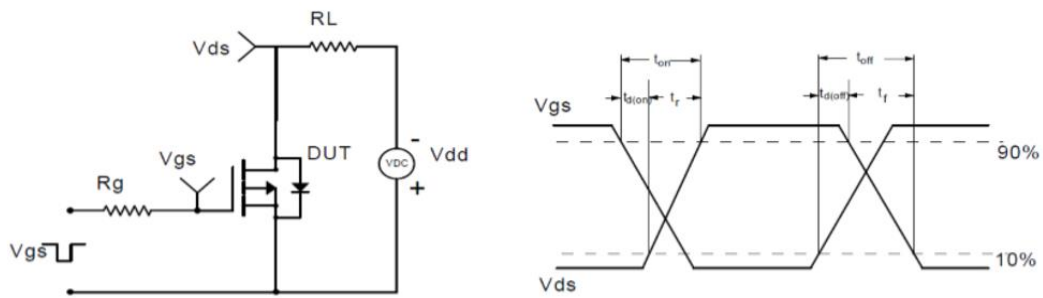


Figure 2: Resistive Switching Test Circuit & Waveform

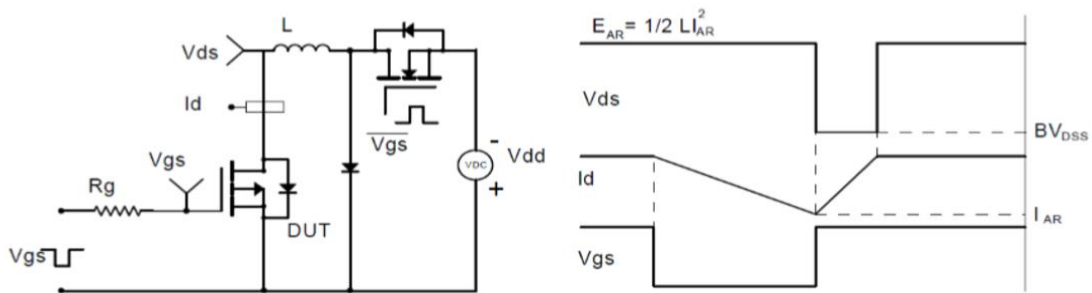


Figure 3: Unclamped Inductive Switching Test Circuit & Waveform

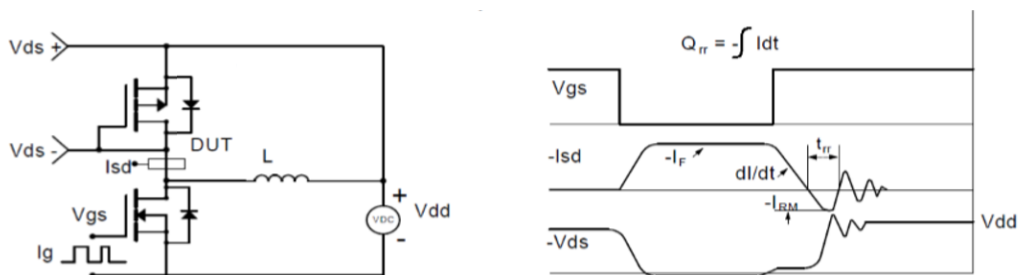
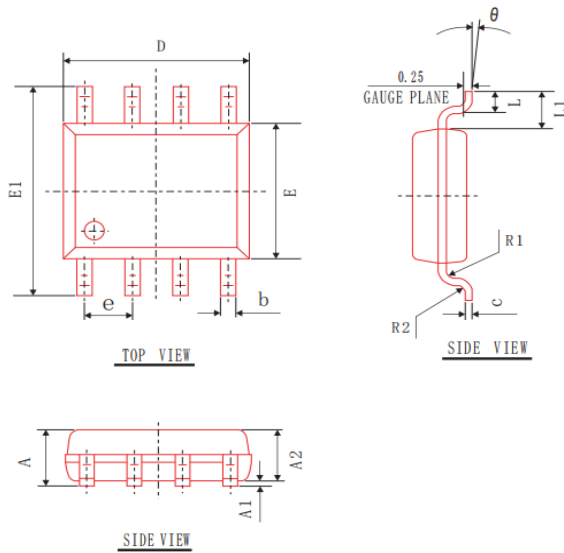


Figure 4: Diode Recovery Test Circuit & Waveform



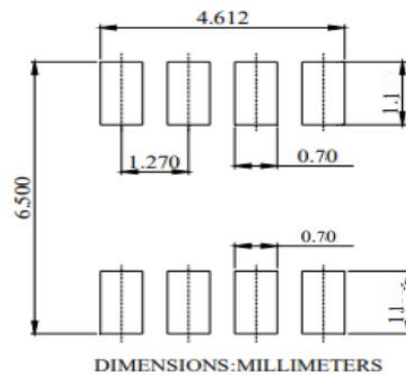
Package Mechanical Data(SOP-8L)



COMMON DIMENSIONS
(UNITS OF MEASURE=mm)

SYMBOL	MIN	NOM	MAX
A	1.40	1.60	1.80
A1	0.05	0.15	0.25
A2	1.35	1.45	1.55
b	0.30	0.40	0.50
c	0.153	0.203	0.253
D	4.80	4.90	5.00
E	3.80	3.90	4.00
E1	5.80	6.00	6.20
L	0.45	0.70	1.00
θ	2°	4°	6°
L 1	1.04 REF		
e	1.27 BSC		
R1	0.07 TYP		
R2	0.07 TYP		

Recommended Footprint



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